

# High Voltage Power Transistors

## DPAK For Surface Mount Applications

Designed for line operated audio output amplifier, SWITCHMODE™ power supply drivers and other switching applications.

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves (“-1” Suffix)
- Lead Formed Version in 16 mm Tape and Reel (“T4” Suffix)
- Electrically Similar to Popular TIP47, and TIP50
- 250 and 400 V (Min) —  $V_{CEO(sus)}$
- 1 A Rated Collector Current

### MAXIMUM RATINGS

Rating	Symbol	MJD47	MJD50	Unit
Collector–Emitter Voltage	$V_{CEO}$	250	400	Vdc
Collector–Base Voltage	$V_{CB}$	350	500	Vdc
Emitter–Base Voltage	$V_{EB}$	5		Vdc
Collector Current — Continuous Peak	$I_C$	1 2		Adc
Base Current	$I_B$	0.6		Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	15 0.12		Watts W/ $^\circ\text{C}$
Total Power Dissipation* @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.56 0.0125		Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +150		$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	8.33	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Ambient*	$R_{\theta JA}$	80	$^\circ\text{C}/\text{W}$
Lead Temperature for Soldering Purpose	$T_L$	260	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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### OFF CHARACTERISTICS

Collector–Emitter Sustaining Voltage (1) ( $I_C = 30 \text{ mAdc}, I_B = 0$ )	MJD47 MJD50	$V_{CEO(sus)}$	250 400	— —	Vdc
Collector Cutoff Current ( $V_{CE} = 150 \text{ Vdc}, I_B = 0$ ) ( $V_{CE} = 300 \text{ Vdc}, I_B = 0$ )	MJD47 MJD50	$I_{CEO}$	— —	0.2 0.2	mAdc

\*When surface mounted on minimum pad sizes recommended.

(continued)

(1) Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

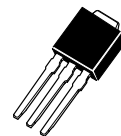
## MJD47\* MJD50\*

\*ON Semiconductor Preferred Device

**NPN SILICON  
POWER TRANSISTORS  
1 AMPERE  
250, 400 VOLTS  
15 WATTS**

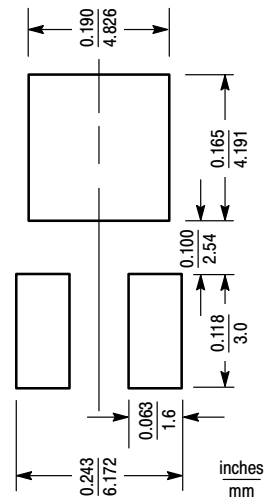


CASE 369A-13



CASE 369-07

### MINIMUM PAD SIZES RECOMMENDED FOR SURFACE MOUNTED APPLICATIONS



# MJD47 MJD50

## ELECTRICAL CHARACTERISTICS – continued ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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### OFF CHARACTERISTICS — continued

Collector Cutoff Current ( $V_{CE} = 350\text{ Vdc}$ , $V_{BE} = 0$ ) ( $V_{CE} = 500\text{ Vdc}$ , $V_{BE} = 0$ )	MJD47 MJD50	$I_{CES}$	— 0.1	mAdc
Emitter Cutoff Current ( $V_{BE} = 5\text{ Vdc}$ , $I_C = 0$ )		$I_{EBO}$	— 1	mAdc

### ON CHARACTERISTICS (1)

DC Current Gain ( $I_C = 0.3\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ ) ( $I_C = 1\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ )	$h_{FE}$	30 10	150 —	—
Collector–Emitter Saturation Voltage ( $I_C = 1\text{ Adc}$ , $I_B = 0.2\text{ Adc}$ )	$V_{CE(sat)}$	—	1	Vdc
Base–Emitter On Voltage ( $I_C = 1\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ )	$V_{BE(on)}$	—	1.5	Vdc

### DYNAMIC CHARACTERISTICS

Current Gain — Bandwidth Product ( $I_C = 0.2\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 2\text{ MHz}$ )	$f_T$	10	—	MHz
Small–Signal Current Gain ( $I_C = 0.2\text{ Adc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1\text{ kHz}$ )	$h_{fe}$	25	—	—

(1) Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

## TYPICAL CHARACTERISTICS

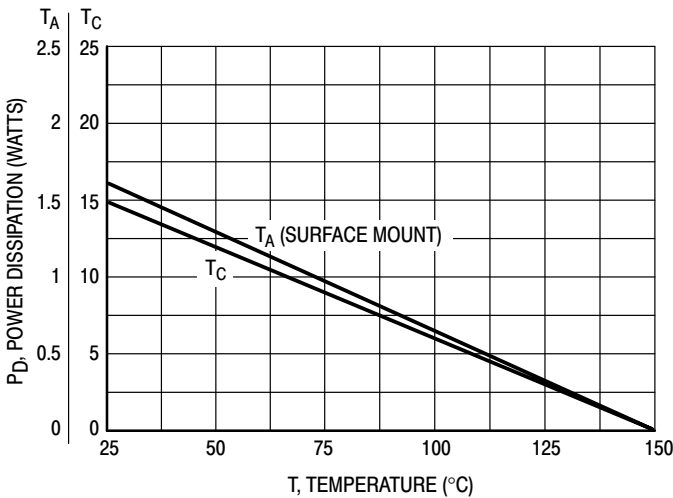


Figure 1. Power Derating

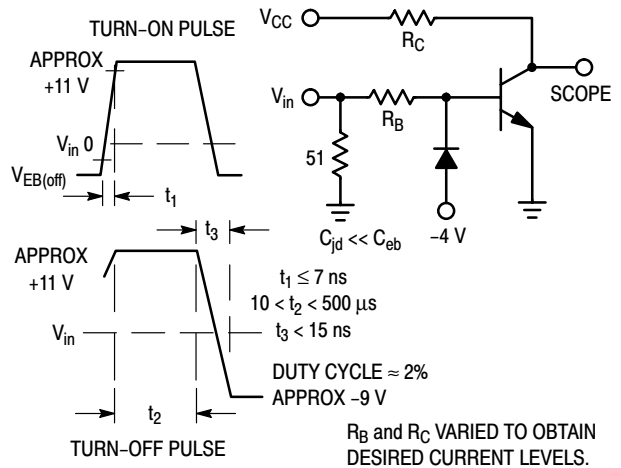


Figure 2. Switching Time Equivalent Circuit

# MJD47 MJD50

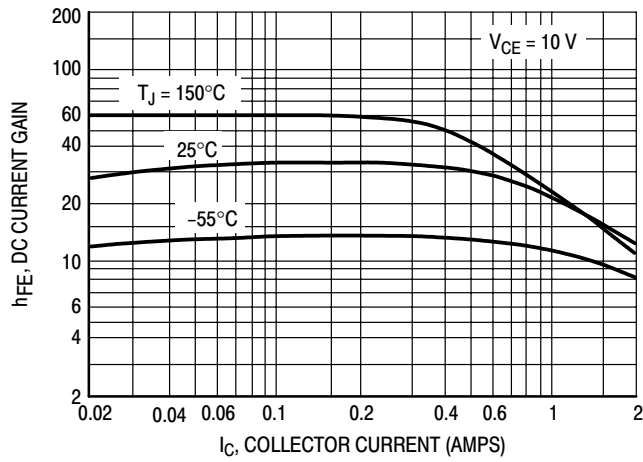


Figure 3. DC Current Gain

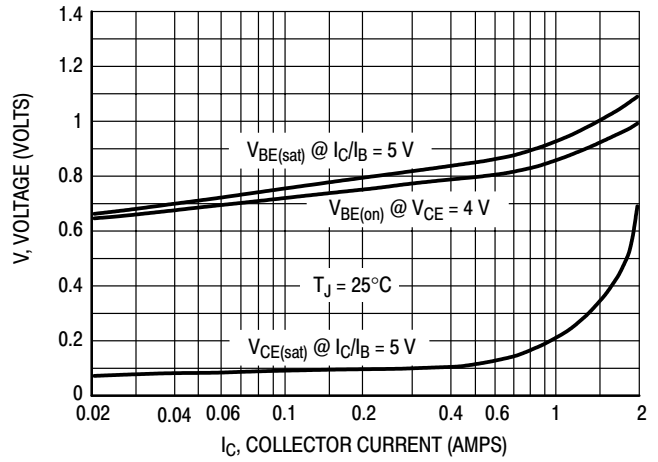


Figure 4. "On" Voltages

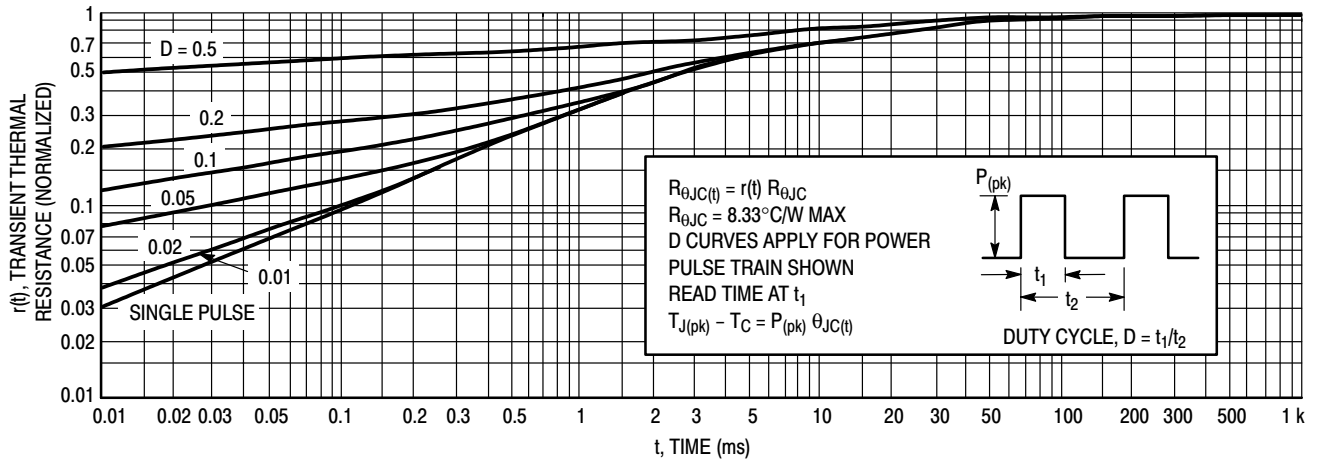
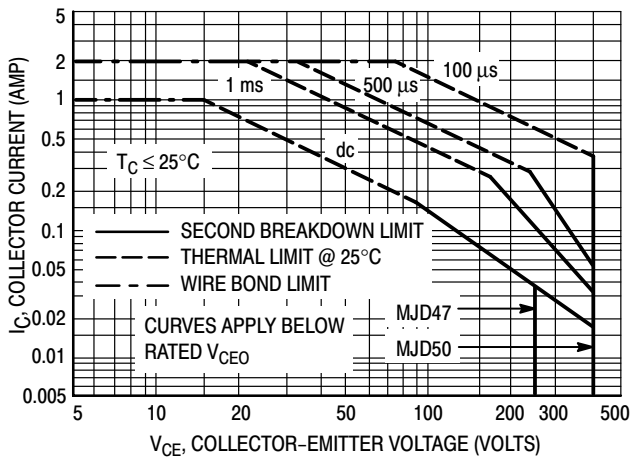


Figure 5. Thermal Response

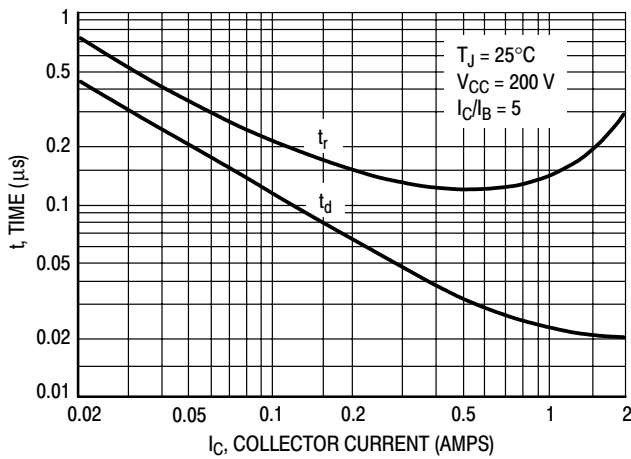
# MJD47 MJD50



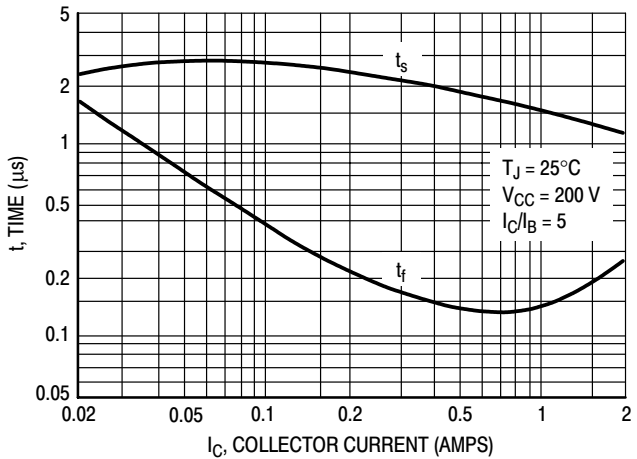
**Figure 6. Active Region Safe Operating Area**

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



**Figure 7. Turn-On Time**

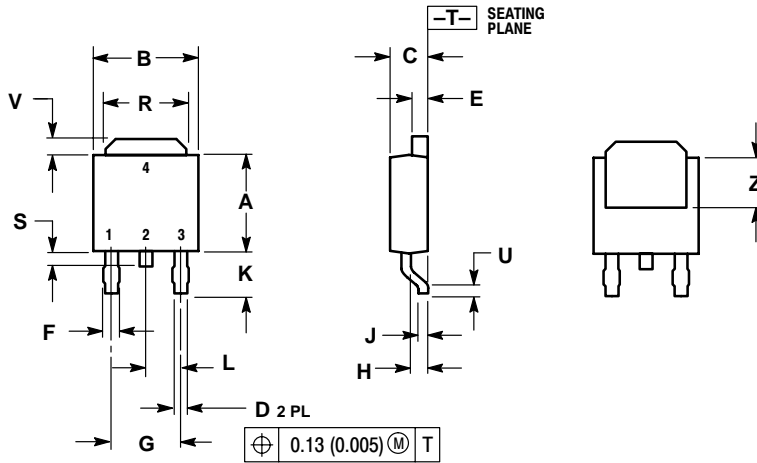


**Figure 8. Turn-Off Time**

# MJD47 MJD50

## PACKAGE DIMENSIONS

### DPAK CASE 369A-13 ISSUE AA



NOTES:

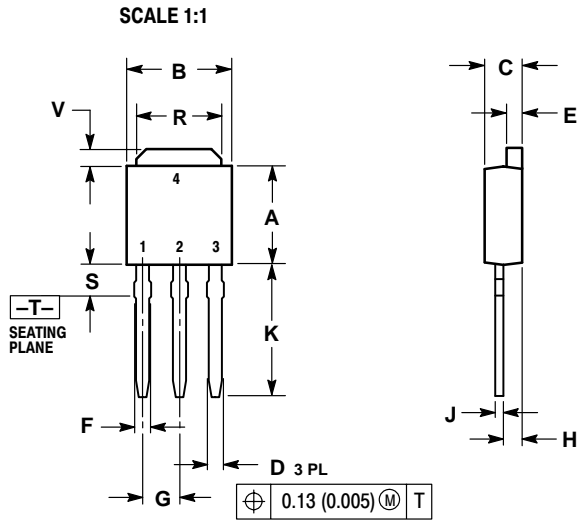
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.250	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.033	0.040	0.84	1.01
F	0.037	0.047	0.94	1.19
G	0.180 BSC		4.58 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.175	0.215	4.45	5.46
S	0.020	0.050	0.51	1.27
U	0.020	---	0.51	---
V	0.030	0.050	0.77	1.27
Z	0.138	---	3.51	---

# MJD47 MJD50

## PACKAGE DIMENSIONS

### DPAK CASE 369-07 ISSUE M




NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.250	5.97	6.35
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C	0.086	0.094	2.19	2.38
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F	0.037	0.047	0.94	1.19
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.175	0.215	4.45	5.46
S	0.050	0.090	1.27	2.28
V	0.030	0.050	0.77	1.27

# Notes

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